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Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

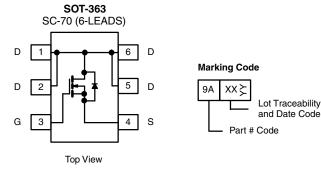
PRODUCT SUMMARY				
V _{DS} (V)	60			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.140			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.200			
I _D (A)	1.6			
Configuration	Single			

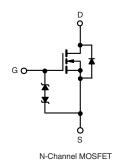
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- AEC-Q101 Qualifiedd
- 100 % R_g Tested
- Typical ESD Protection: 800 V
- Compliant to RoHS Directive 2002/95/EC









ORDERING INFORMATION	
Package	SC-70
Lead (Pb)-free and Halogen-free	SQ1420EEH-T1-GE3

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	60	V	
Gate-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Currents	T _C = 25 °C	1	1.6	Δ.	
Continuous Drain Current ^a	T _C = 125 °C	I _D	1.6		
Continuous Source Current (Diode Conduction) ^a Pulsed Drain Current ^b		I _S	1.6	Α	
		I _{DM}	6.7		
Maximum Power Dissipation ^b	T _C = 25 °C	D	3.3	W	
Maximum Fower Dissipation	T _C = 125 °C	P_{D}	1.1	VV	
Operating Junction and Storage Temperat	ure Range	T _J , T _{sta}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	125	°C/W
Junction-to-Foot (Drain)		R_{thJF}	45	C/ VV

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static						l .	
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0$, $I_D = 250 \mu A$		60	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	· V _{GS} , I _D = 250 μA	1.5	2.0	2.5	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$		-	-	± 500	nA
		V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	1	mA
		V _{GS} = 0 V	V _{DS} = 60 V			1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μΑ
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	1	-	-	Α
Drain-Source On-State Resistance ^a	(* /	V _{GS} = 10 V	I _D = 1.2 A	-	0.100	0.140	Ω
		V _{GS} = 10 V	I _D = 1.2 A, T _J = 125 °C	-	-	0.245	
	R _{DS(on)}	V _{GS} = 10 V	I _D = 1.2 A, T _J = 175 °C	-	-	0.308	
		V _{GS} = 4.5 V	I _D = 1 A	-	0.152	0.200	
Forward Transconductanceb	9 _{fs}	V _{DS}	= 15 V, I _D = 1 A	-	2.9	-	S
Dynamic ^b	<u> </u>						
Input Capacitance	C _{iss}			-	172	215	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	36	45	pF
Reverse Transfer Capacitance	C _{rss}]		-	24	30	
Total Gate Charge ^c	Qg			-	2.7	4	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 4.5 V	$V_{DS} = 30 \text{ V}, I_D = 2.8 \text{ A}$	-	0.7	-	nC
Gate-Drain Charge ^c	Q _{gd}]		-	1.4	-	
Gate Resistance	Rg	f = 1 MHz		1.1	1.6	2.1	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	12	18	
Rise Time ^c	t _r	$V_{DD} = 30 \text{ V}, \text{ R}_L = 30 \Omega$ $I_D \cong 1 \text{ A}, \text{ V}_{GEN} = 4.5 \text{ V}, \text{ R}_g = 1 \Omega$		-	21	32	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	8	12	
Fall Time ^c	t _f			-	7	11	
Source-Drain Diode Ratings and Chara	acteristics ^b				•		
Pulsed Current ^a	I _{SM}			-	-	6.7	Α
Forward Voltage	V_{SD}	I _F =	= 0.8 A, V _{GS} = 0	-	0.8	1.2	V

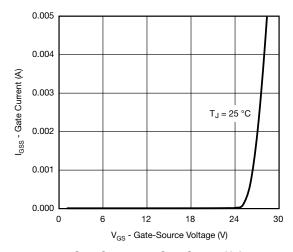
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

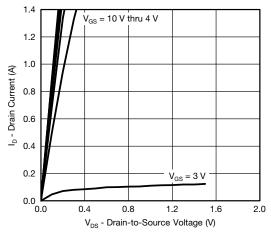
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



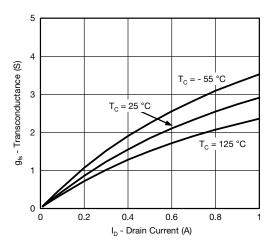
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



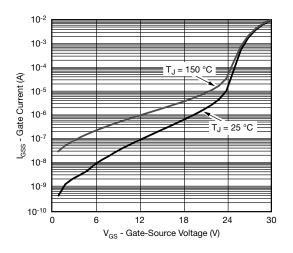
Gate Current vs. Gate-Source Voltage



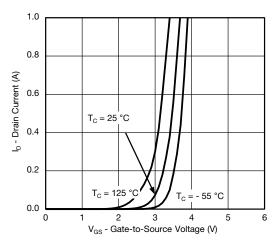
Output Characteristics



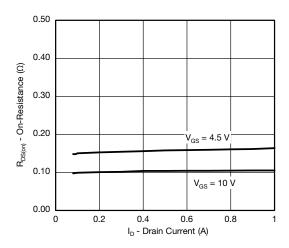
Transconductance



Gate Current vs. Gate-Source Voltage



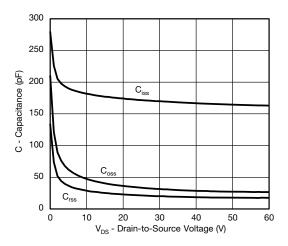
Transfer Characteristics



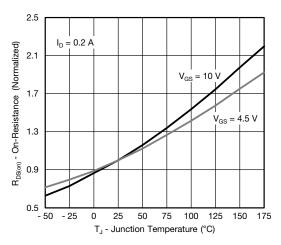
On-Resistance vs. Drain Current



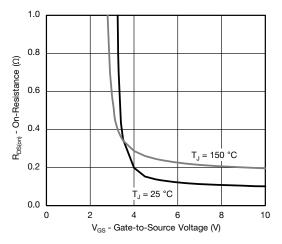
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



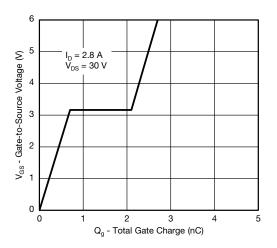
Capacitance



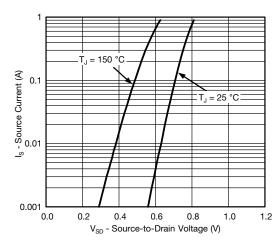
On-Resistance vs. Junction Temperature



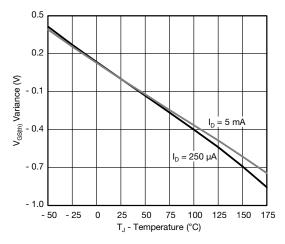
On-Resistance vs. Gate-to-Source Voltage



Gate Charge



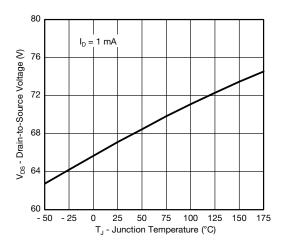
Source Drain Diode Forward Voltage



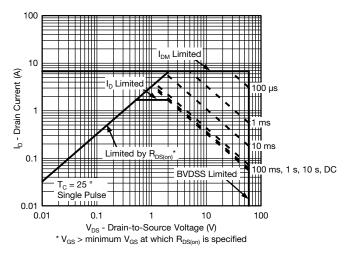
Threshold Voltage



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

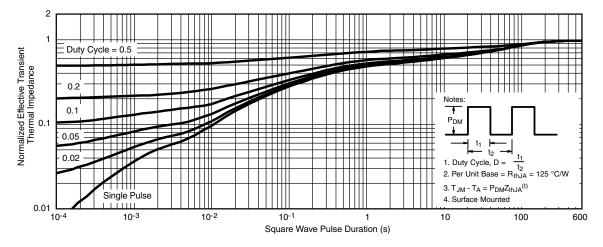


Drain Source Breakdown vs. Junction Temperature

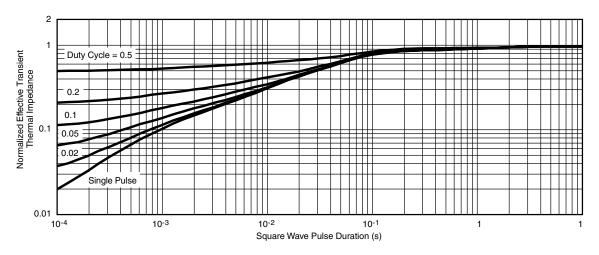




THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg265730.





SC-70: 6-LEADS





	MIL	LIMET	ERS	INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.90	-	1.10	0.035	_	0.043	
A ₁	-	-	0.10	-	-	0.004	
A_2	0.80	-	1.00	0.031	-	0.039	
b	0.15	-	0.30	0.006	_	0.012	
С	0.10	-	0.25	0.004	_	0.010	
D	1.80	2.00	2.20	0.071	0.079	0.087	
Ε	1.80	2.10	2.40	0.071	0.083	0.094	
E ₁	1.15	1.25	1.35	0.045	0.049	0.053	
е		0.65BSC			0.026BSC	;	
e ₁	1.20	1.30	1.40	0.047	0.051	0.055	
L	0.10	0.20	0.30	0.004	0.008	0.012	
9	7°Nom				7°Nom		



RECOMMENDED MINIMUM PADS FOR SC-70: 6-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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